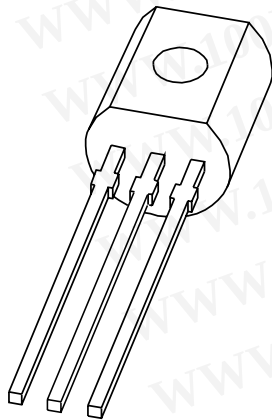


DATA SHEET



PN2907A PNP switching transistor

Product data sheet
Supersedes data of 1997 May 05

2004 Oct 11



founded by Philips

PNP switching transistor

PN2907A

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 60 V).

APPLICATIONS

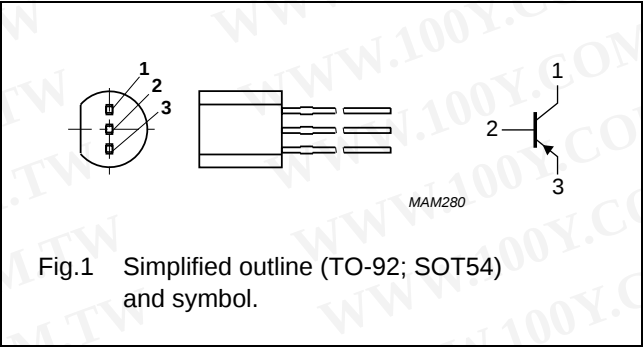
- Switching and linear amplification.

DESCRIPTION

PNP switching transistor in a TO-92; SOT54 plastic package. NPN complement: PN2222A.

PINNING

PIN	DESCRIPTION
1	collector
2	base
3	emitter



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–60	V
V_{CEO}	collector-emitter voltage	open base	–	–60	V
I_C	collector current (DC)		–	–600	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	–	500	mW
h_{FE}	DC current gain	$V_{CE} = -10\text{ V}; I_C = -150\text{ mA}$	100	300	
f_T	transition frequency	$V_{CE} = -20\text{ V}; I_C = -50\text{ mA}; f = 100\text{ MHz}$	200	–	MHz
t_{off}	turn-off time	$I_{Con} = -150\text{ mA}; I_{Bon} = -15\text{ mA}; I_{Boff} = 15\text{ mA}$	–	365	ns

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PN2907A	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54

PNP switching transistor

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–60	V
V_{CEO}	collector-emitter voltage	open base	–	–60	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–600	mA
I_{CM}	peak collector current		–	–800	mA
I_{BM}	peak base current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	–	500	mW
T_{stg}	storage temperature		–65	+150	$^{\circ}\text{C}$
T_j	junction temperature		–	150	$^{\circ}\text{C}$
T_{amb}	ambient temperature		–65	+150	$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	250	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

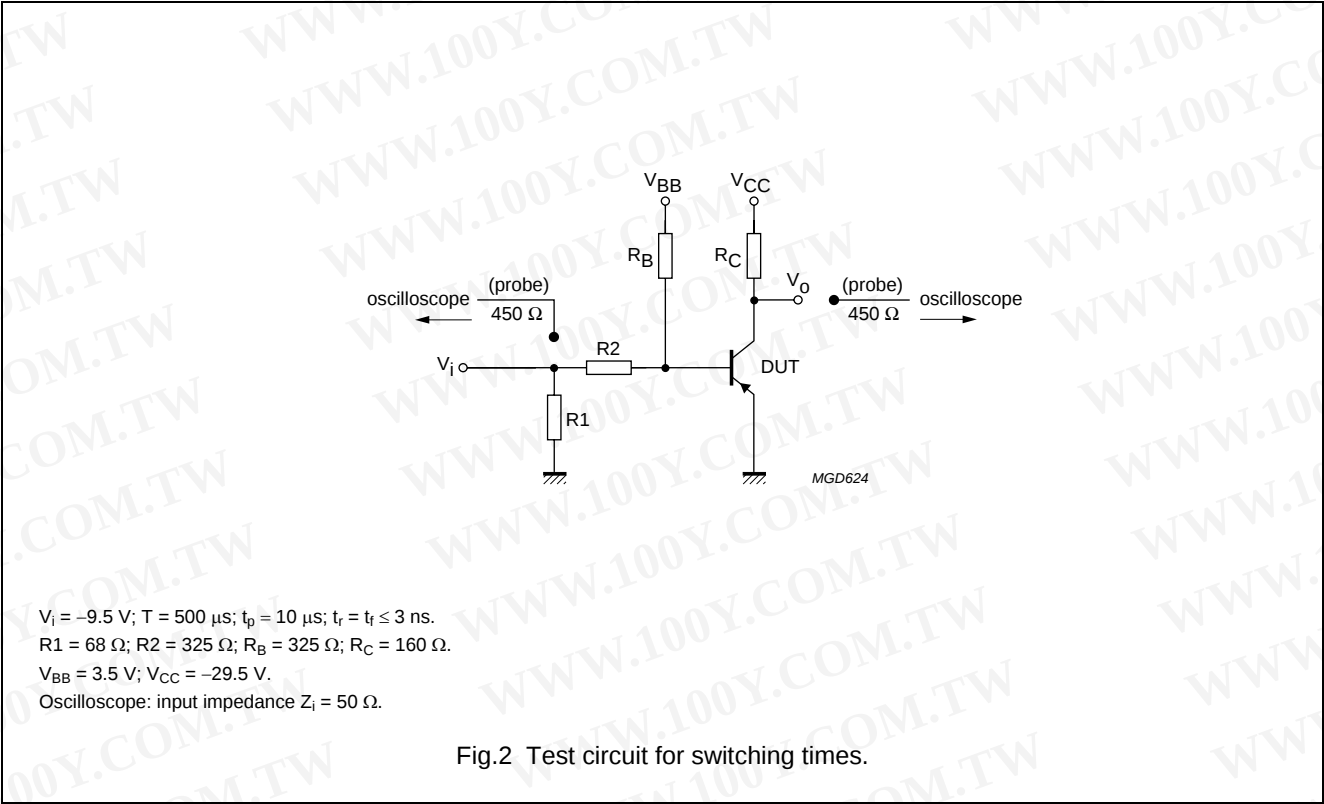
$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = -50\text{ V}; I_E = 0\text{ A}$	–	–10	nA
		$V_{CB} = -50\text{ V}; I_E = 0\text{ A}; T_j = 125\text{ }^{\circ}\text{C}$	–	–10	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}$	–	–50	nA
h_{FE}	DC current gain	$V_{CE} = -10\text{ V}; I_C = -0.1\text{ mA}$	75	–	
		$V_{CE} = -10\text{ V}; I_C = -1\text{ mA}$	100	–	
		$V_{CE} = -10\text{ V}; I_C = -10\text{ mA}$	100	–	
		$V_{CE} = -10\text{ V}; I_C = -150\text{ mA}$	100	300	
		$V_{CE} = -10\text{ V}; I_C = -500\text{ mA}$	50	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -150\text{ mA}; I_B = -15\text{ mA}$	–	–400	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	–	–1.6	V
V_{BEsat}	base-emitter saturation voltage	$I_C = -150\text{ mA}; I_B = -15\text{ mA}$	–	–1.3	V
		$I_C = -150\text{ mA}; I_B = -50\text{ mA}$	–	–2.6	V
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$	–	8	pF
C_e	emitter capacitance	$V_{EB} = -2\text{ V}; I_C = i_c = 0\text{ A}; f = 1\text{ MHz}$	–	30	pF
f_T	transition frequency	$V_{CE} = -20\text{ V}; I_C = -50\text{ mA}; f = 100\text{ MHz}$	200	–	MHz

PNP switching transistor

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SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Switching times (between 10 % and 90 % levels); see Fig.2					
t _{on}	turn-on time	I _{Con} = -150 mA; I _{Bon} = -15 mA; I _{Boff} = 15 mA	—	40	ns
t _d	delay time		—	12	ns
t _r	rise time		—	30	ns
t _{off}	turn-off time		—	365	ns
t _s	storage time		—	300	ns
t _f	fall time		—	65	ns



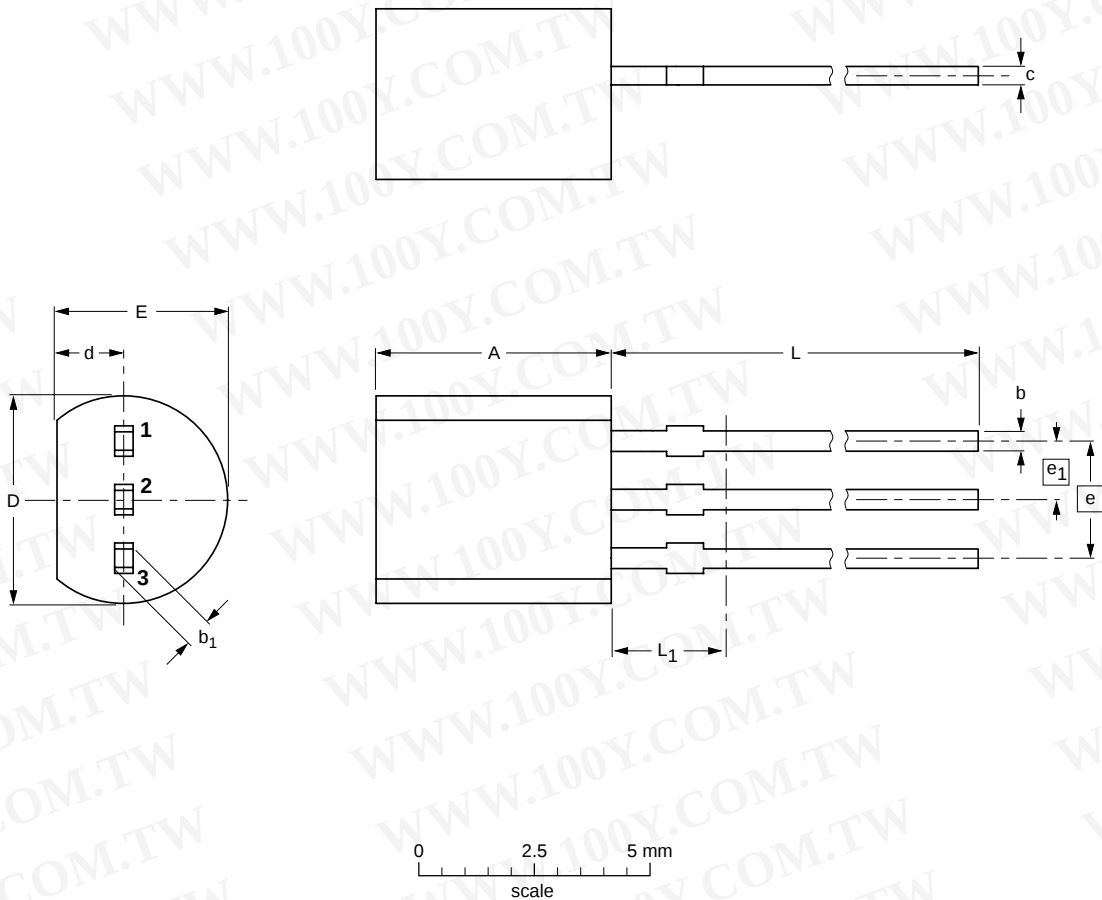
PNP switching transistor

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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b ₁	c	D	d	E	e	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT54		TO-92	SC-43A			04-06-28 04-11-16

PNP switching transistor

PN2907A

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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